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The Conference Theme

Electron Devices and Intellectualization of Everything

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Takanobu Watanabe
(Waseda University)

14:40-15:00

A-2 **(p.24)** **An 800-MHz 8-bit High Speed SAR ADC in 16nm FinFET Process**
Keisuke Okuno, Koji Obata, Takumi Kato and Koji Sushihara
(Panasonic Corporation)

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15:10-15:30

A-3 **(p.26)** **Image Sensor with New Trench-gated Phototransistor**
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Poster Session

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Hibiki Nakano[1], Naoto Matsuo[1], Tadao Takada[1], Kazushige Yamana[1], Akira Heya[1], Tadashi Sato[2] and Shin Yokoyama[2]
([1]University of Hyogo, [2]Hiroshima University)

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Yoshiaki Mori[1], Shingo Sato[1], Yasuhisa Omura[1] and Abhijit Mallik[2]
([1]Kansai University, [2]University of Calcutta)

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Mitsuhiro Urano, Kazuki Ata and Akira Takahashi
(National Institute of Technology, Nara College)

PA-04 (p.38) **Wireless Power Transmission to Thin-Film Devices**
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(Ryukoku University)

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(Ryukoku University)

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Nobuya Fujimoto, Akira Hiroki and Shin Hiratoko
(Kyoto Institute of Technology)

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(Meijo University)

PA-08 (p.46) **Evaluation of PLFSR PUF with Several Implementation Methods for FPGA**
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(Meijo University)

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(Kyoto Institute of Technology)

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(Hosei University)

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Kazuki Ata, Mitsuhiro Urano and Akira Takahashi
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([1]Osaka Institute of Technology, [2]Rigaku Corporation)

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Session B (Compound Devices)

Chairs: Masaaki Kuzuhara / Hiroyuki Sakai

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Toshiyuki Tsuchiya
(Kyoto University)

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Tohru Oka
(TOYODA GOSEI)

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([1]Kyoto University, [2]Nagoya University)

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Keito Kanatani, Satoshi Yoshida, Akio Yamamoto and Masaaki Kuzuhara

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Masataka Sasada, Aki Sasakura, Norifumi Takashima, Hirokuni Tokuda and Masaaki Kuzuhara

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Kuniharu Takei
(Osaka Prefecture University)

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Hideki Iwamoto, Tsutomu Takai, Yuichi Takamine, Masahiro Hiramoto and Masayoshi Koshino
(Murata)

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15:40-16:00

C-4 (p.104) **Hall Effect in Thin-Film Transistor - Sensitivity Dependence on Applied Voltage -**
Takaaki Matsumoto[1], Akito Yoshikawa[1], Tokiyoshi Matsuda[1], Mutsumi Kimura[1], Tokuro Ozawa[2], Koji Aoki[2] and Chih-Che Kuo[2]
([1]Ryukoku University, [2]AU Optronics Corporation)

16:00-16:20

C-5 (p.106) **MEMS based fabrication of conformal electrode pairs for thermotunneling cooling**
Amit Banerjee, Yoshikazu Hirai, Toshiyuki Tsuchiya and Osamu Tabata
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Shota Nakajima, Jo Shiomi, Kaoru Yamashita and Minoru Noda
(Kyoto Institute of Technology)

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Poster Viewing Session

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Closing

18:00-18:20 Award and Closing: Mutsumi Kimura (Ryukoku University)